

ELECTRON BEAM NANOLITHOGRAPHY SYSTEM (RAITH VOYAGER)



Key Specifications:

- Beam energy and current range: 50 KV, 50pA-40 nA
- Beam size: less than 2.5 nm
- Scan frequency: 50 MHz
- Write-field size (Max): 500 x 500 microns
- Field stitch and overlay accuracy: less than 35 nm
- Minimum guaranteed linewidth: 10 nm
- Wafer/sample size: 0.3 x 0.3 in sample size to 6 in wafer